

P-Channel 1.5 V (G-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
- 8	0.023 at V _{GS} = - 4.5 V	- 7	28
	0.029 at V _{GS} = - 2.5 V	- 6.2	
	0.036 at V _{GS} = - 1.8 V	- 5.2	
	0.048 at V _{GS} = - 1.5 V	- 5	

FEATURES

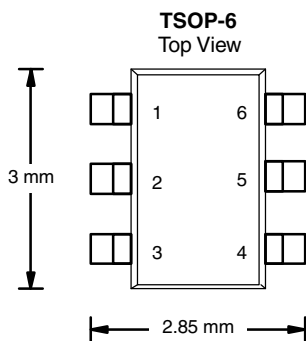
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET: 1.5 V Rated
- Ultra-Low On-Resistance
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



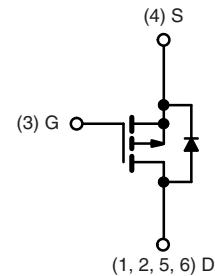
RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Load Switch for Portable Devices



Ordering Information: Si3499DV-T1-E3 (Lead (Pb)-free)
Si3499DV-T1-GE3 (Lead (Pb)-free and Halogen-free)
Marking Code: 99xxx



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	- 8		V	
Gate-Source Voltage	V _{GS}	± 5			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	- 7	- 5.3	A
		T _A = 85 °C	- 3.6	- 3.9	
Pulsed Drain Current	I _{DM}	- 20			
Continuous Source Current (Diode Conduction) ^a	I _S	- 1.7	- 0.9		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	2	1.1	W
		T _A = 85 °C	1	0.6	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 s	R _{thJA}	45	62.5	°C/W
	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	25	30	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

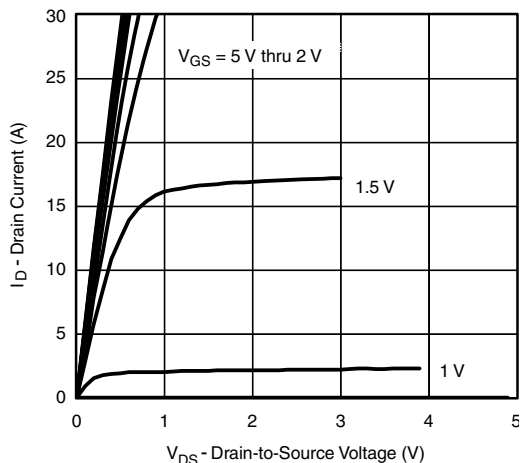
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.35		-0.75	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	-20			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -7\text{ A}$		0.019	0.023	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -6.2\text{ A}$		0.024	0.029	
		$V_{GS} = -1.8\text{ V}, I_D = -5.2\text{ A}$		0.028	0.036	
		$V_{GS} = -1.5\text{ V}, I_D = -3\text{ A}$		0.035	0.048	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -5\text{ V}, I_D = -7\text{ A}$		28		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.7\text{ A}, V_{GS} = 0\text{ V}$		-0.63	-1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -4\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -7\text{ A}$		28	42	nC
Gate-Source Charge	Q_{gs}			2.9		
Gate-Drain Charge	Q_{gd}			5.8		
Gate Resistance	R_g		4	8.5	13	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -4\text{ V}, R_L = 4\text{ }\Omega$ $I_D = -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 6\text{ }\Omega$		27	40	ns
Rise Time	t_r			65	100	
Turn-Off Delay Time	$t_{d(off)}$			210	315	
Fall Time	t_f			110	165	
Source-Drain Reverse Recovery Time	t_{rr}		$I_F = -1.7\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		40	

Notes:

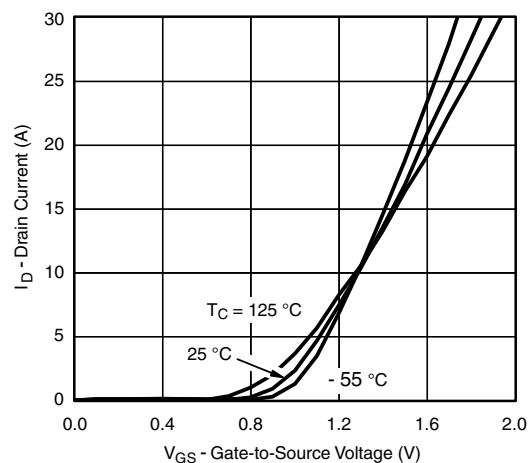
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

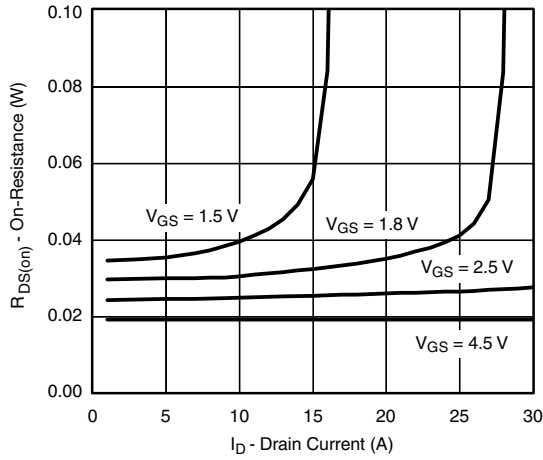


Output Characteristics

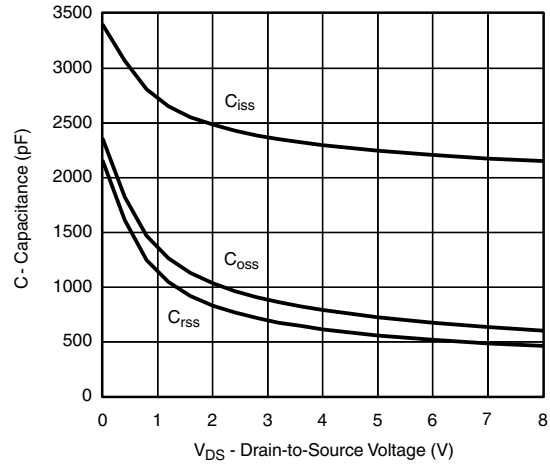


Transfer Characteristics

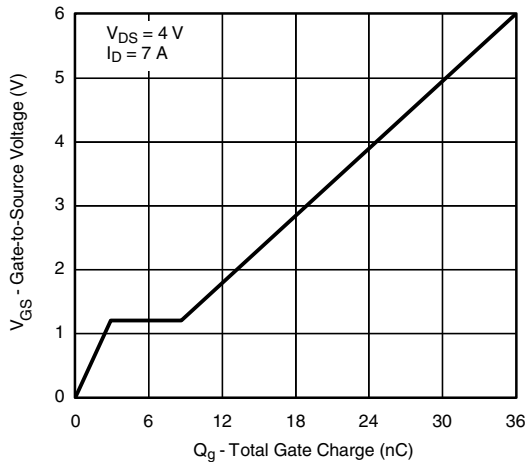
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



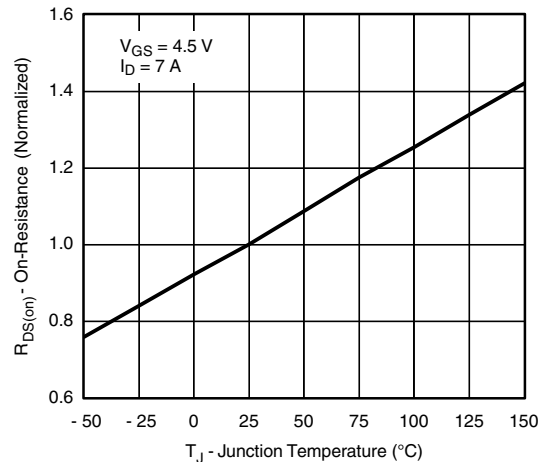
On-Resistance vs. Drain Current



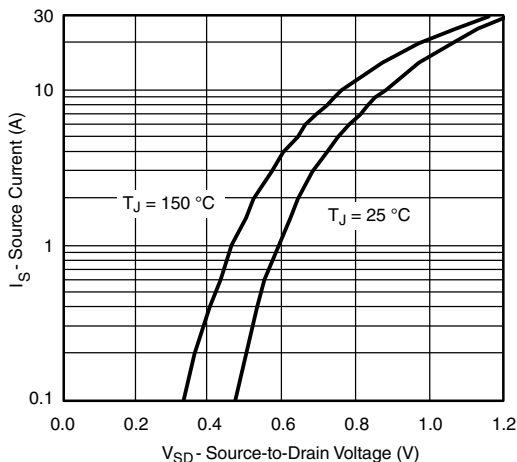
Capacitance



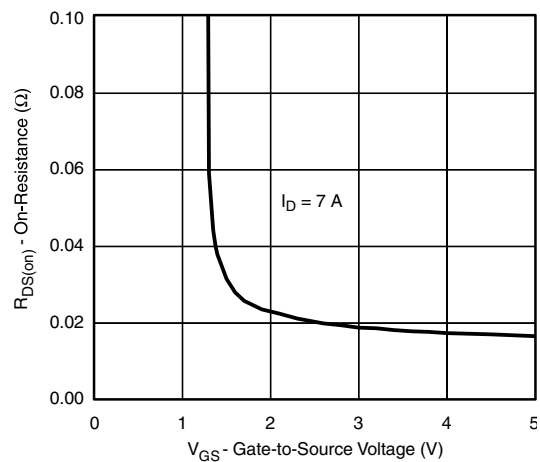
Gate Charge



On-Resistance vs. Junction Temperature

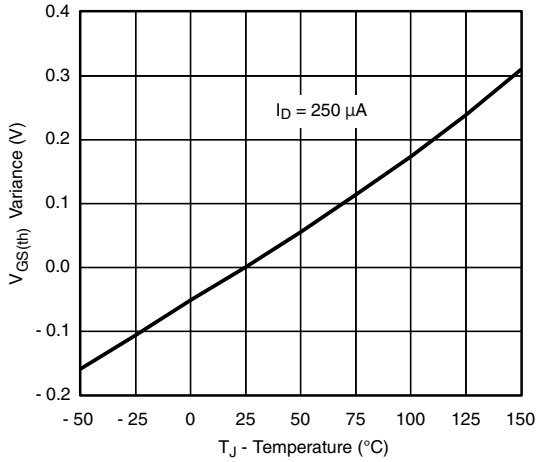


Source-Drain Diode Forward Voltage

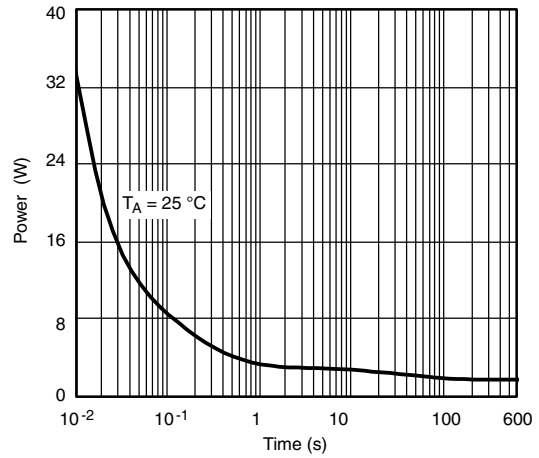


On-Resistance vs. Gate-to-Source Voltage

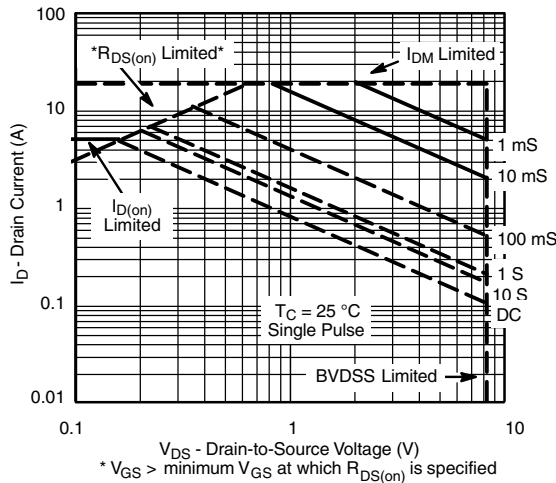
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



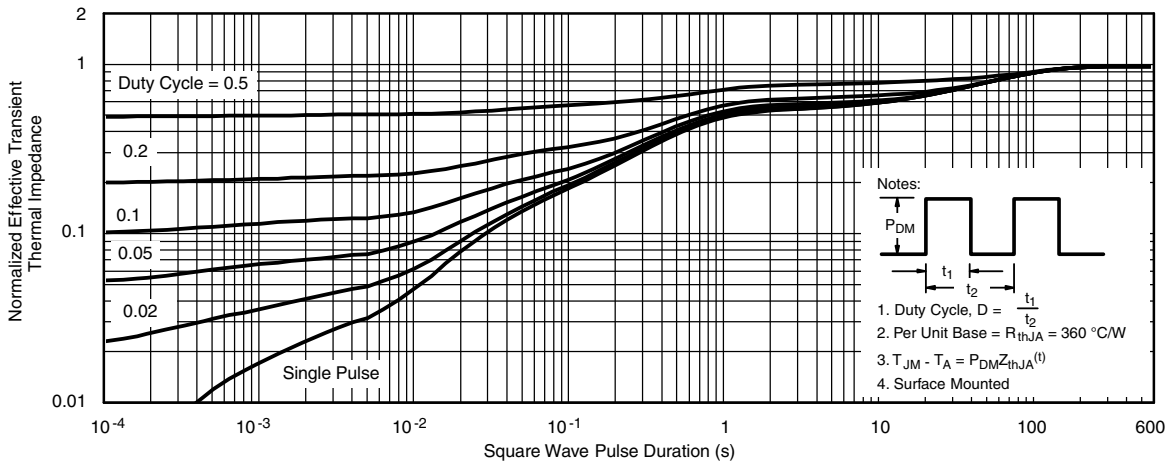
Threshold Voltage



Single Pulse Power

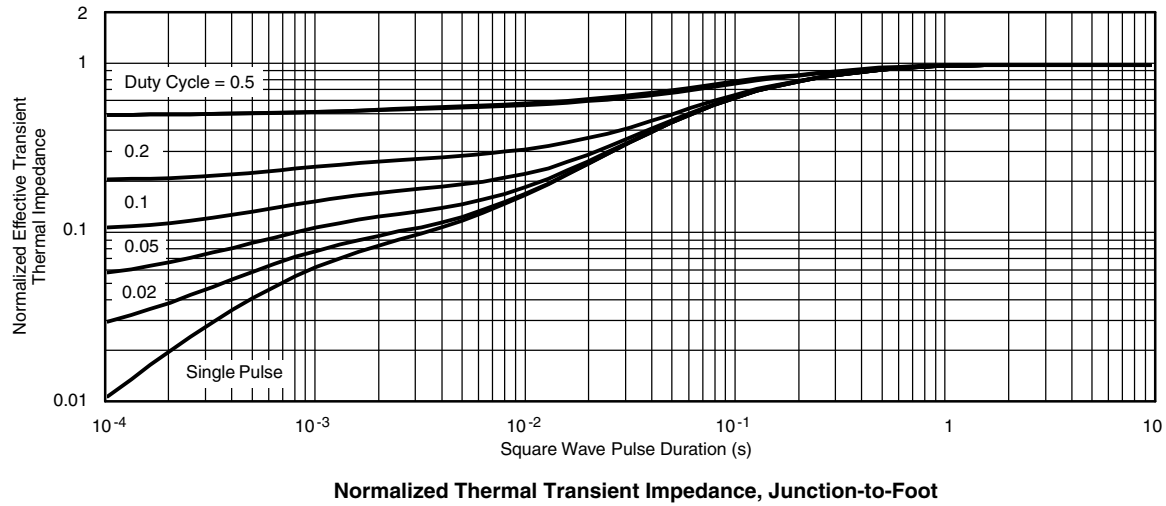


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

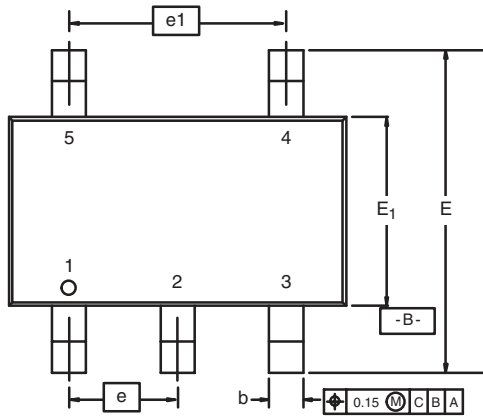
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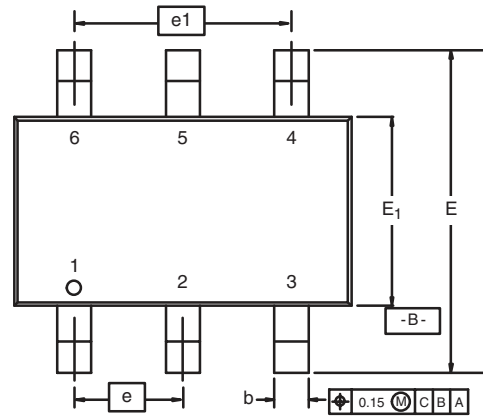
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TSOP: 5/6-LEAD

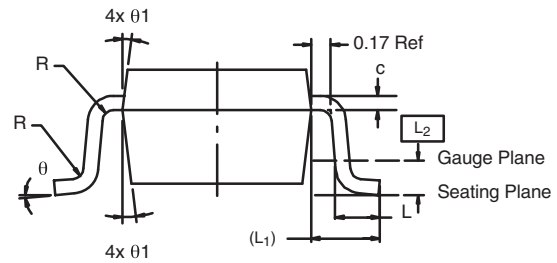
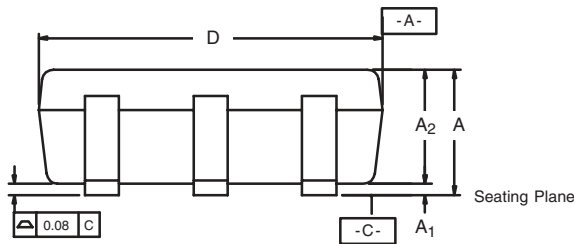
JEDEC Part Number: MO-193C



5-LEAD TSOP



6-LEAD TSOP



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A₁	0.01	-	0.10	0.0004	-	0.004
A₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L₁	0.60 Ref			0.024 Ref		
L₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ₁	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						



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